

Response under 37 C.F.R. §1.111
Serial No. 10/614,227
Attorney Docket No. 030823

AMENDMENTS TO THE SPECIFICATION

Please amend the title as follows:

SEMICONDUCTOR DEVICE HAVING LOW INTERFACE STATE DENSITY AND
METHOD FOR FABRICATING THE SAME

Please amend the paragraph starting on page 13, line 12 as follows:

The gate electrode of polysilicon is formed of Si, which is a IV group element. The gate insulation film of Al₂O₃ contains Al, which is a ~~V-group~~ III group element. When the gate insulation film contacts the gate electrode, Al non-combined bonds are present in the interface between the gate insulation film and the gate electrode, which is a factor for large fixed charge amount.